



**VISHAY MAS**  
**GENERAL SEMICONDUCTOR**

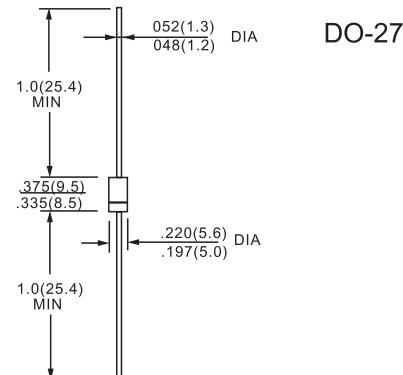
**80SQ035 THRU 80SQ045**

**35V-45V 8.0A**

## FEATURES

- 175°C  $T_J$  operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term

Designed and qualified for industrial level



Dimensions in inches and (millimeters)

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

### VOLTAGE RATINGS

PARAMETER	SYMBOL	80SQ030	80SQ035	80SQ040	80SQ045	UNITS
Maximum DC reverse voltage	$V_R$	30	35	40	45	V
Maximum working peak reverse voltage	$V_{RWM}$					

### ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average forward current See fig. 5	$I_{F(AV)}$	50 % duty cycle at $T_C = 119^\circ\text{C}$ , rectangular waveform		8	A
Maximum peak one cycle non-repetitive surge current See fig. 7	$I_{FSM}$	5 $\mu\text{s}$ sine or 3 $\mu\text{s}$ rect. pulse		2400	
		10 ms sine or 6 ms rect. pulse		380	
Non-repetitive avalanche energy	$E_{AS}$	$T_J = 25^\circ\text{C}$ , $I_{AS} = 1.6 \text{ A}$ , $L = 7.8 \text{ mH}$		10	mJ
Repetitive avalanche current	$I_{AR}$	Current decaying linearly to zero in 1 $\mu\text{s}$ Frequency limited by, $T_J$ maximum $V_A = 1.5 \times V_R$ typical		1.6	A

### ELECTRICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum forward voltage drop See fig. 1	$V_{FM}^{(1)}$	8 A	$T_J = 25^\circ\text{C}$	0.53	V	
		16 A		0.60		
		8 A	$T_J = 125^\circ\text{C}$	0.44		
		16 A		0.55		
Maximum reverse leakage current See fig. 2	$I_{RM}^{(1)}$	$T_J = 25^\circ\text{C}$	$V_R = \text{Rated } V_R$	2	mA	
		$T_J = 125^\circ\text{C}$		15		
Maximum junction capacitance	$C_T$	$V_R = 5 \text{ V}_{DC}$ , (test signal range 100 kHz to 1 MHz) $25^\circ\text{C}$		900	pF	
Typical series inductance	$L_S$	Measured lead to lead 5 mm from package body		10.0	nH	
Maximum voltage rate of change	$dV/dt$	Rated $V_R$		10 000	V/ $\mu\text{s}$	

### THERMAL - MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum junction and storage temperature range	$T_J, T_{Stg}$			- 55 to 175	°C
Maximum thermal resistance, junction to lead	$R_{thJL}$	DC operation; see fig. 4 1/8" lead length		8.0	°C/W
Typical thermal resistance, junction to air	$R_{thJA}$			44	
Approximate weight				1.4	g
				0.049	oz.
Marking device		Case style DO-204AR (JEDEC)		80SQ030	
				80SQ035	
				80SQ040	
				80SQ045	



RATINGS AND CHARACTERISTIC CURVES 80SQ035 THRU 80SQ045

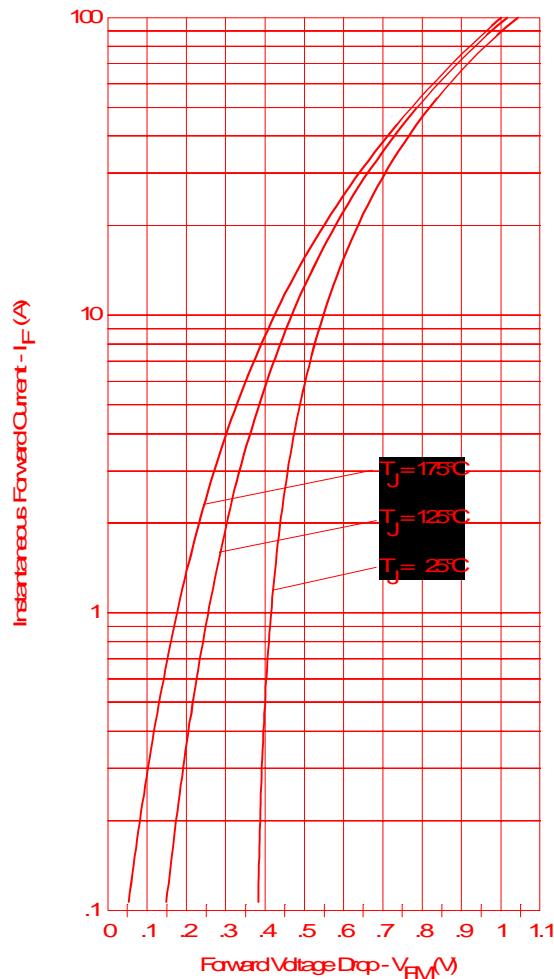


Fig. 1 - Maximum Forward Voltage Drop Characteristics

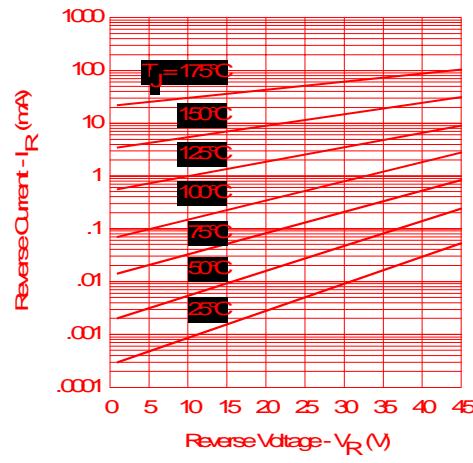


Fig. 2 - Typical Values of Reverse Current Vs. Reverse Voltage

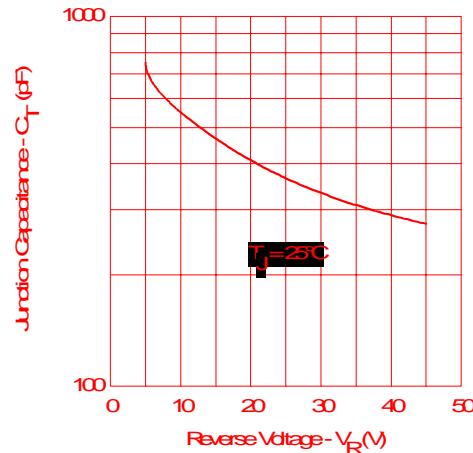


Fig. 3 - Typical Junction Capacitance Vs. Reverse Voltage

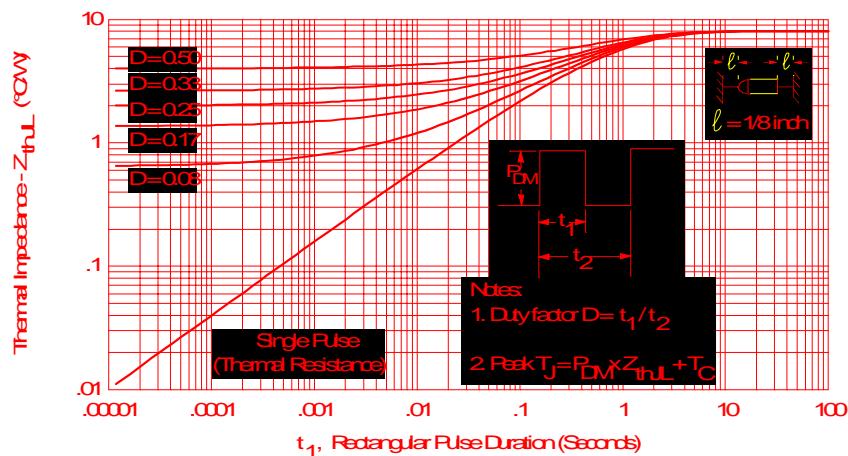


Fig. 4 - Maximum Thermal Impedance  $Z_{thJL}$  Characteristics



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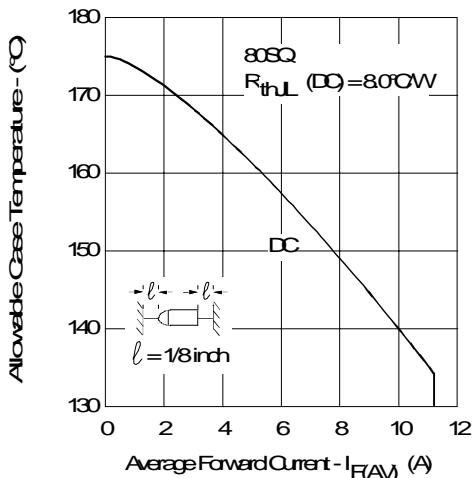


Fig. 5 - Maximum Allowable Case Temperature  
Vs. Average Forward Current

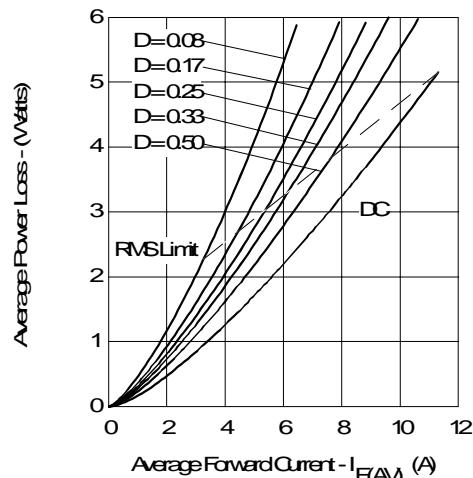


Fig. 6 - Forward Power Loss Characteristics

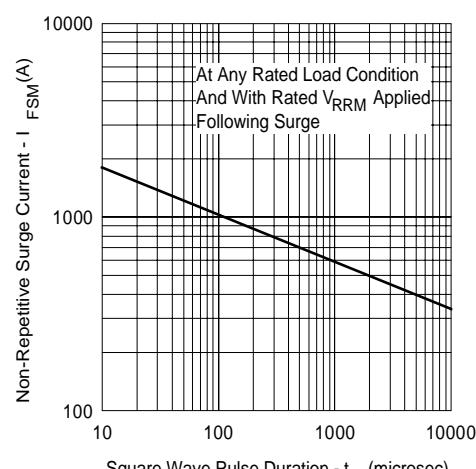


Fig. 7 - Maximum Non-Repetitive Surge Current

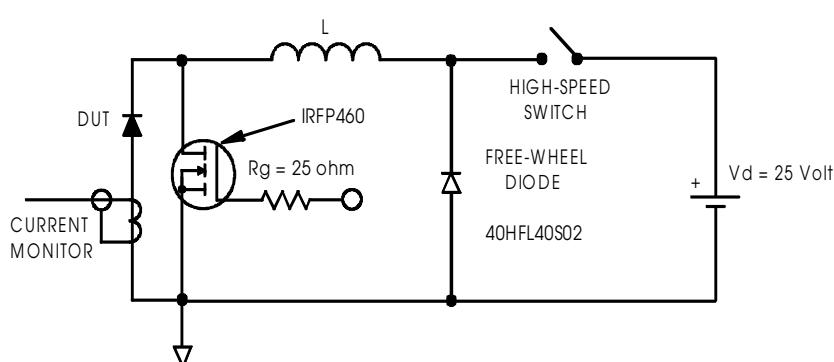


Fig. 8 - Unclamped Inductive Test Circuit